1SS133M

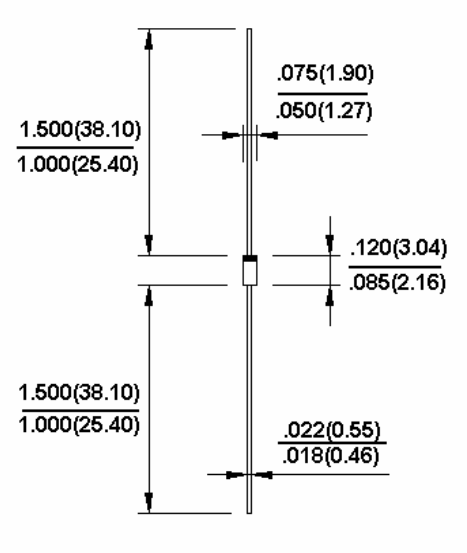
300mW Hermetically Sealed Glass Switching Diode

DO-34



Features

- ✧ Fast switching device(T_{RR}<4.0nS)
- ✧ DO-34 package (JEDEC DO-204)
- ✧ Through-hole device type mounting
- ✧ Hermetically sealed glass
- ✧ Compression bonded construction
- ✧ All external surfaces are corrosion resistant and leads are readily solderable
- ✧ RoHS compliant
- ✧ Solder hot dip Tin (Sn) lead finish
- ✧ Cathode indicated by polarity band



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Maximum Ratings

Type Number	Symbol	Value	Units
Power Dissipation	Pd	300	mW
Working Inverse Voltage	W_{IV}	90	V
Average Rectified Current	Io	150	mA
Non-Repetitive Peak Forward Current	I_{FM}	450	mA
Peak Forward surge Current	I_{FSURGE}	2	A
Operating Junction Temperature	T_J	+ 175	°C
Storage Temperature Range	T_{STG}	-65 to + 200	°C

Electrical Characteristics

Type Number		Symbol	Min	Max	Units
Breakdown Voltage	I_R=500nA	B_V	80		V
Forward Voltage	I_F =100mA	V_F		1.2	V
Reverse Leakage Current	V_R=80V	I_R		500	nA
Junction Capacitance	V_R=0, f=1.0MHz	Cj	-	4.0	pF
Reverse Recovery Time (Note 1)		trr	-	4.0	nS

Notes: 1. Reverse Recovery Test Conditions: I_F=I_R=10mA, R_L=100Ω, I_{RR}=1mA

Version: A07

RATINGS AND CHARACTERISTIC CURVES (1SS133M)

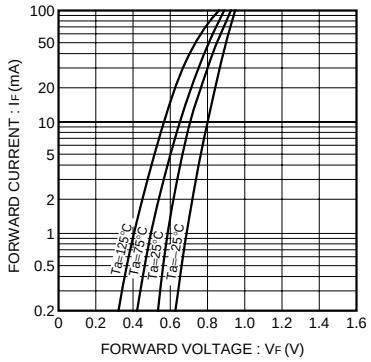


Fig.1 Forward characteristics

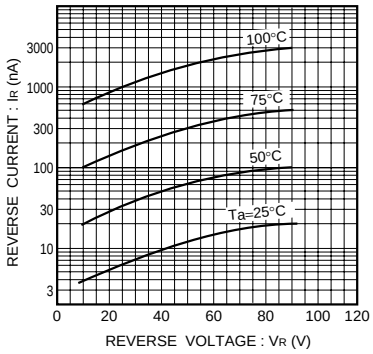


Fig.2 Reverse characteristics

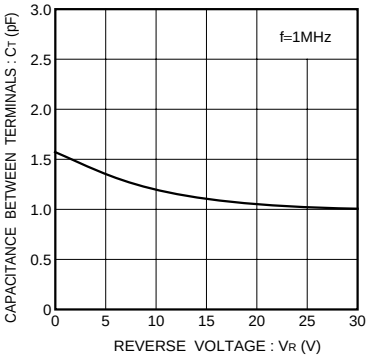


Fig.3 Capacitance between terminals characteristics

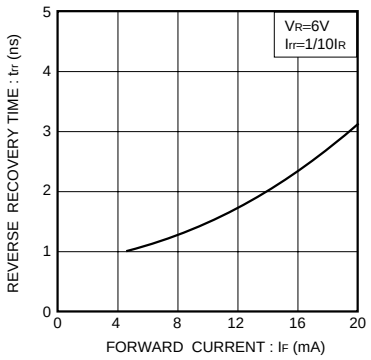


Fig.4 Reverse recovery time characteristics

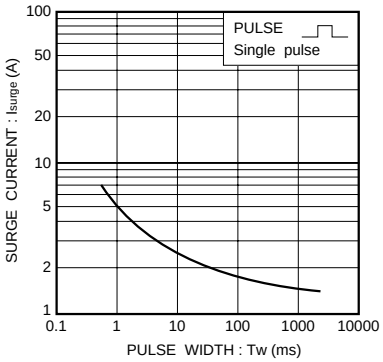


Fig.5 Surge current characteristics

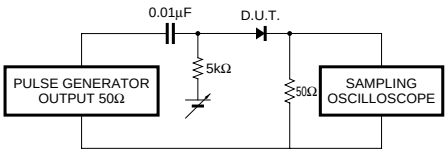


Fig.6 Reverse recovery time (t_{rr}) measurement circuit